### PATENT COOPERATION TREATY

From the INTERNATIONAL SEARCHING AUTHORITY		· .	ESE		
To: OKABE MASAO		PCT	18 47 VA 5		
No.602, Fuji Bldg., 2-3, Marunouchi 3-chome, Chiyoda-ku, Tokyo 100-0005 JAPAN	WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY  (PCT Rule 43bis.1)				
	Date of mailing (day/month/year)	25. 5. 200	04		
Applicant's or agent's file reference CFO17899WO	FOR FURTHER ACTION  See paragraph 2 below				
International application No.	e (day/month/year)	Priority date (day/month)	•		
International Patent Classification (IPC) or both national classific Int.Cl 7 H01L27/146,G01T1/24,H04N5/3		<u> </u>	-		
Applicant CANON KABUSHII	KI KAISHA	·			
1. This opinion contains indications relating to the following items:    Box No. I Basis of the opinion					
Name and mailing address of the ISA/JP	Authorized officer		4L 8122		
Japan Patent Office	KYOICHI S		3498		
3-4-3, Kasumigaseki, Chiyoda-ku, Tokyo 100-8915, Japan	Lelephone No. +81	-3-3581-1101 Ext. 3	7-2-9-9		

# WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2004/001423

Box	No. I	Basis of the opinion	
1.	With	regard to the language, this opinion has been established	ed on the basis of the international application in the language in
•		h it was filed, unless otherwise indicated under this item	
		This opinion has been established on the basis of a tran	nslation from the original language into the following language slation furnished for the purposes of international search (under
l		Rules 12.3 and 23.1(b)).	
1			
2.	With	regard to any nucleotide and/or amino acid sequence	e disclosed in the international application and necessary to the
İ		ed invention, this opinion has been established on the base	JID 01.
l	a. typ	e of material	
		a sequence listing	
	L	table(s) related to the sequence listing	
	b. for	mat of material	
	101 	in written format	
	F	in computer readable form	
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		- Care to the	
-	c. tin	ne of filing/furnishing contained in the international application as filed.	
-	F	contained in the international application as filed.  filed together with the international application in	
	۲	furnished subsequently to this Authority for the pu	
3.,		filed or furnished, the required statements that the info	copy of a sequence listing and/or table relating thereto has been ormation in the subsequent or additional copies is identical to that
		in the application as filed or does not go beyond the application	pplication as filed, as appropriate, were furnished.
		tional account	
4.	Add	itional comments:	•
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## WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.
PCT/JP2004/ 001423

. Statement			,
Novelty (N)	Claims	2-6,8-12,14-18	YES
	Claims	1,7,13,19,20	NО
Inventive step (IS)	Claims		YES
	Claims	1-20	NO
Industrial applicability (IA)	Claims ·	1-20	YES
	Claims		NO

2. Citations and explanations

D1:JP 2002-26300 A(SHARP CORPORATION)2002.01.25,

D2:JP 2000-12866 A(TOSHIBA CORPORATION)2000.01.14,

D3:JP 63-172470 A(FUJITSU LIMITED)1988.07.16

#### **Novelty**

The subject matters of claims 1,7,13,19,20 do not appear to be novel with respect to D1. D1 discloses a photoelectric converter, comprising a plurality of pixels each comprising a sensor element for converting incident light into an electrical signal and a thin film transistor connected to the sensor element.

And D1( [0057] paragraph) teaches that it is possible to form a staggered thin film tran sistor (a top gate type structure TFT).

### Inventive step

The subject matters of claims 2-6,8-12,14-16 do not appear to involve an inventive step in view of D1 and D2.

D2 discloses a photoelectric converter, comprising a double gate type structure TFT (a p lurality of thin film transistors which are connected in series with one another and which use a same gate wiring).

And D2(figs.9-11) discloses a photoelectric converter, comprising a resetting thin film transistor and an amplifying thin film transistor.

The skilled person in the art would easily conceive the idea of employing the feature in D2 to substitute the feature disclosed in D1.

The subject matters of claims 17,18 do not appear to involve an inventive step in view of D1.D2 and D3.

D3 discloses an insulating layer formed between the insulating substrate and the thin fil m transistors.

The skilled person in the art would easily conceive the idea of employing the feature in D3 to substitute the feature disclosed in D1 and D2.